

G2N3906

PNP EPITAXIAL PLANAR TRANSISTOR

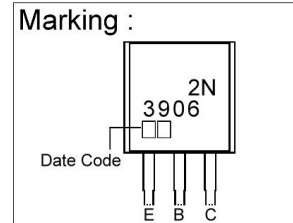
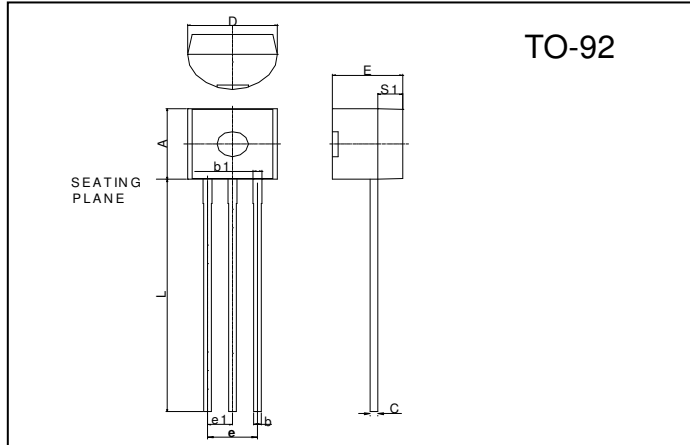
Description

The G2N3906 is designed for general purpose switching and amplifier applications.

Features

- *Pb-free package are available
- *Collector-Emitter Voltage: $V_{CEO} = -40V$
- *Collect Dissipation: $P_c (max) = 625mW$
- *Complementary to G2N3904

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

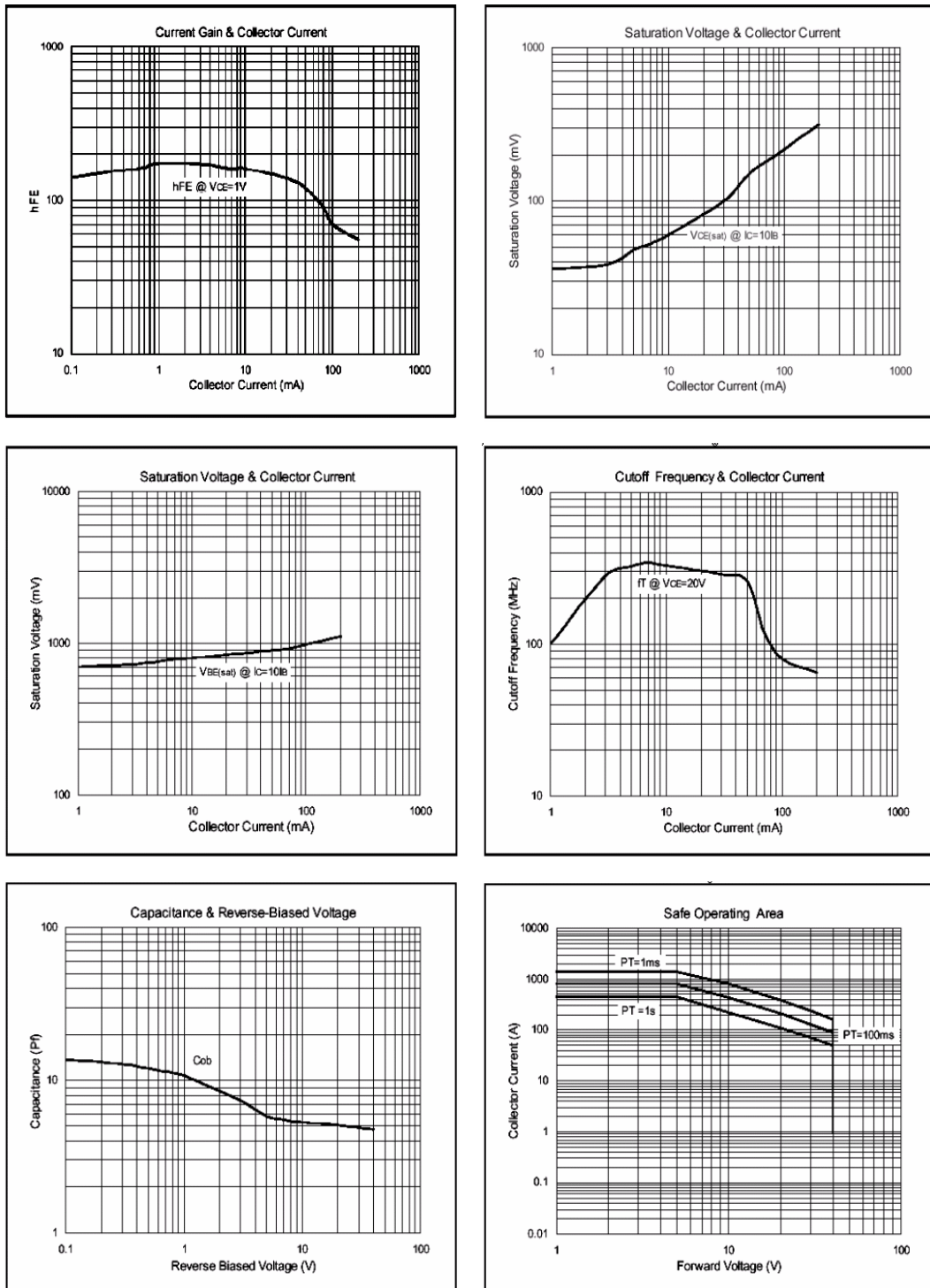
Absolute Maximum Ratings ($T_a = 25^\circ C$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-40	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collect Current(DC)	I_c	-200	mA
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ C$
Total Power Dissipation	P_D	625	mW

Electrical Characteristics ($T_a = 25^\circ C$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CBO}	-40	-	-	V	$I_C = -10\mu A, I_E = 0$
V_{CEO}	-40	-	-	V	$I_C = -1mA, I_B = 0$
V_{EBO}	-5	-	-	V	$I_E = -10\mu A, I_C = 0$
I_{CEX}	-	-	-50	nA	$V_{CE} = -30V, V_{EB} = -3V$
I_{EBO}	-	-	-50	nA	$V_{EB} = -3V$
$V_{CE(sat)1}$	-	-	-0.25	V	$I_C = -10mA, I_B = -1mA$
$V_{CE(sat)2}$	-	-	-0.4	V	$I_C = -50mA, I_B = -5mA$
$V_{BE(sat)1}$	-0.65	-	-0.85	V	$I_C = -10mA, I_B = -1mA$
$V_{BE(sat)2}$	-	-	-0.95	V	$I_C = -50mA, I_B = -5mA$
h_{FE1}	60	-	-		$V_{CE} = -1V, I_C = -0.1mA$
h_{FE2}	80	-	-		$V_{CE} = -1V, I_C = -1mA$
h_{FE3}	100	-	300		$V_{CE} = -1V, I_C = -10mA$
h_{FE4}	60	-	-		$V_{CE} = -1V, I_C = -50mA$
h_{FE5}	30	-	-		$V_{CE} = -1V, I_C = -100mA$
f_T	250	-	-	MHz	$V_{CE} = -20V, I_E = -10mA, f = 100MHz$
C_{ob}	-	-	4.5	pF	$V_{CB} = -10V, f = 100KHz$
C_{ib}	-	-	10	pF	$V_{EB} = -0.5V, f = 100KHz$
t_d	-	-	35	ns	$V_{CC} = -3V, V_{BE(OFF)} = -0.5V, I_C = -10mA, I_{B1} = -1mA$
t_r	-	-	35	ns	$V_{CC} = -3V, V_{BE(OFF)} = -0.5V, I_C = -10mA, I_{B1} = -1mA$
t_{stg}	-	-	225	ns	$V_{CC} = -3V, I_C = -10mA, I_{B1} = -I_{B2} = -1mA$
t_f	-	-	75	ns	$V_{CC} = -3V, I_C = -10mA, I_{B1} = -I_{B2} = -1mA$

Characteristics Curve



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